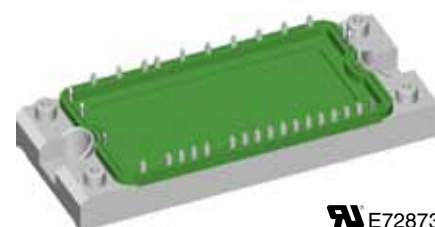
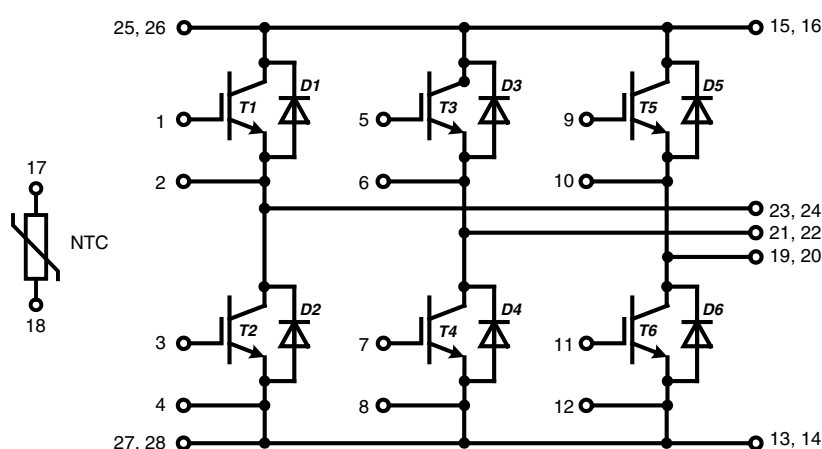


Six-Pack Trench IGBT

$$\begin{aligned} I_{C25} &= 110\text{ A} \\ V_{CES} &= 1200\text{ V} \\ V_{CE(sat)} \text{ typ.} &= 1.7\text{ V} \end{aligned}$$

Part name (Marking on product)

MWI 75-12T7T



E72873

Pin configuration see outlines.

Features:

- Trench IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E2-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			110		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			75		A
I_{CM}	max. pulsed collector current	$t_p = 1 \text{ ms}$ $T_C = 80^{\circ}\text{C}$			150		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			355		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}$ on chip level	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.7 2.0	2.15		V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 3 \text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5	5.8	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	tbd	4		mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20 \text{ V}$			400		nA
C_{ies}	input capacitance	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		5350			pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 600 \text{ V}; V_{GE} = \pm 15 \text{ V}; I_C = 75 \text{ A}$		700			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600 \text{ V}; I_C = 75 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 4.7 \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	290			ns
t_r	current rise time			50			ns
$t_{d(off)}$	turn-off delay time			520			ns
t_f	current fall time			90			ns
E_{on}	turn-on energy per pulse			7			mJ
E_{off}	turn-off energy per pulse			9.5			mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15 \text{ V}; R_G = 4.7 \Omega$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1150 \text{ V}$		100		A
SCSOA	short circuit safe operating area						
t_{SC}	short circuit duration	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
I_{SC}	short circuit current	$R_G = 4.7 \Omega$; non-repetitive		300			A
R_{thJC}	thermal resistance junction to case	(per IGBT)			0.35		K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			135		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			90		A
V_F	forward voltage	$I_F = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.95	2.2		V V
Q_{rr}	reverse recovery charge	$V_R = 600 \text{ V}$ $di_F/dt = -1600 \text{ A}/\mu\text{s}$ $I_F = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	12.5			μC
I_{RM}	max. reverse recovery current			100			A
t_{rr}	reverse recovery time			350			ns
E_{rec}	reverse recovery energy			4			mJ
R_{thJC}	thermal resistance junction to case	(per diode)			0.4		K/W

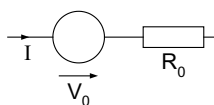
Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
R_{25} $B_{25/50}$	resistance	$T_C = 25^{\circ}\text{C}$	4.75	5.0 3375	5.25	$\text{k}\Omega$ K

Module

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	Unit
T_{VJ}	operating temperature		-40		125	$^{\circ}\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^{\circ}\text{C}$
T_{stg}	storage temperature		-40		125	$^{\circ}\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			2500	V~
CTI	comparative tracking index				200	
M_d	mounting torque (M5)		2.7		3.3	Nm
d_S	creep distance on surface		6			mm
d_A	strike distance through air		6			mm
$R_{pin-chip}$	resistance pin to chip			2.5		$\text{m}\Omega$
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02		K/W
Weight				180		g

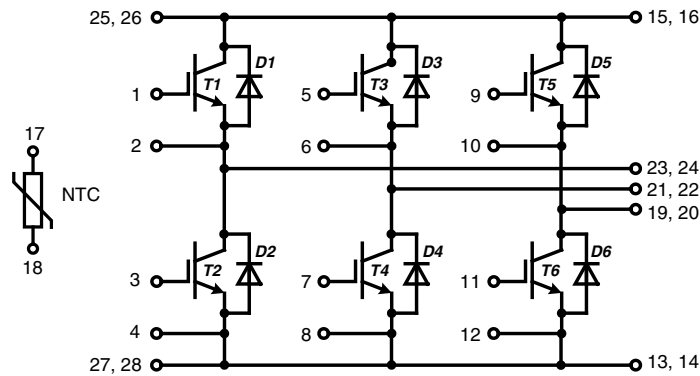
Equivalent Circuits for Simulation



Ratings

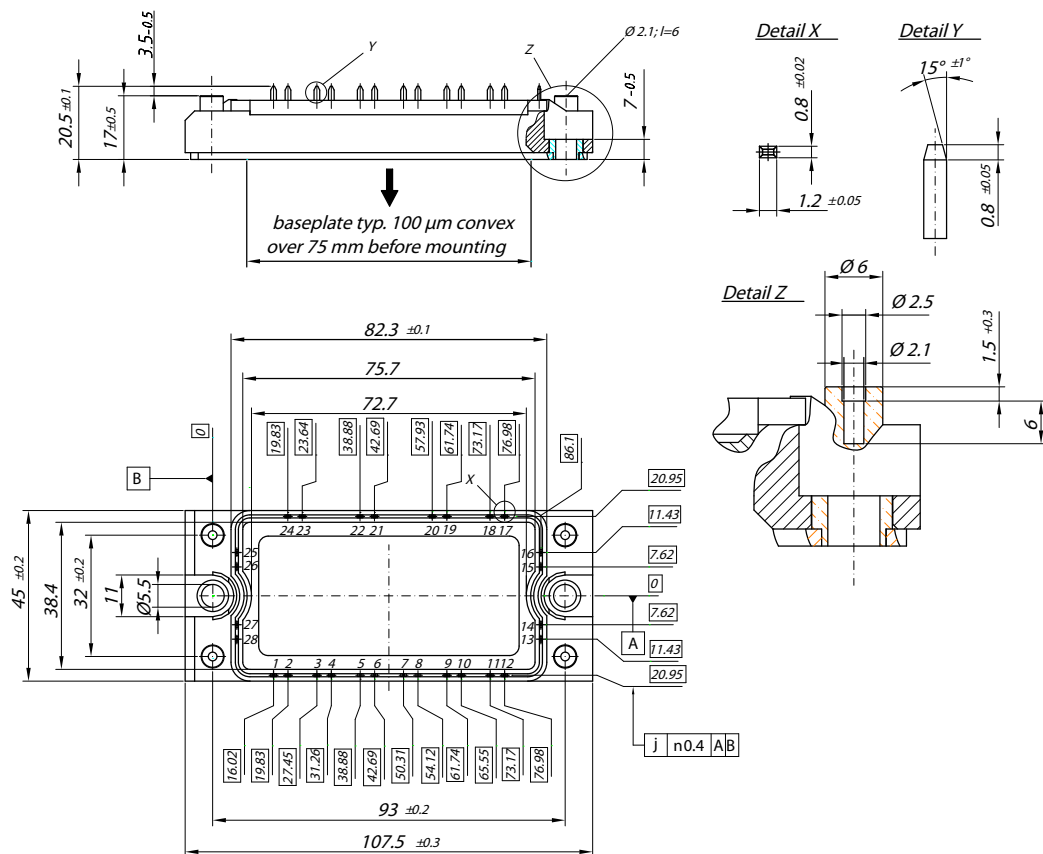
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_0 R_0	IGBT	T1 - T6 $T_{VJ} = 125^{\circ}\text{C}$		1.0 13.3		V $\text{m}\Omega$
V_0 R_0	Diode	D1 - D6 $T_{VJ} = 150^{\circ}\text{C}$		1.09 9.1		V $\text{m}\Omega$

Circuit Diagram

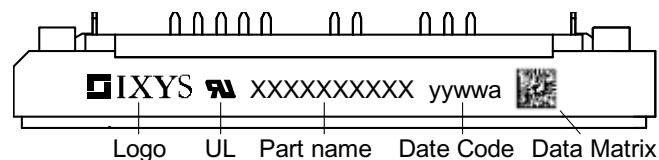


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MWI 75-12T7T	MWI75-12T7T	Box	6	501979

Inverter T1 - T6

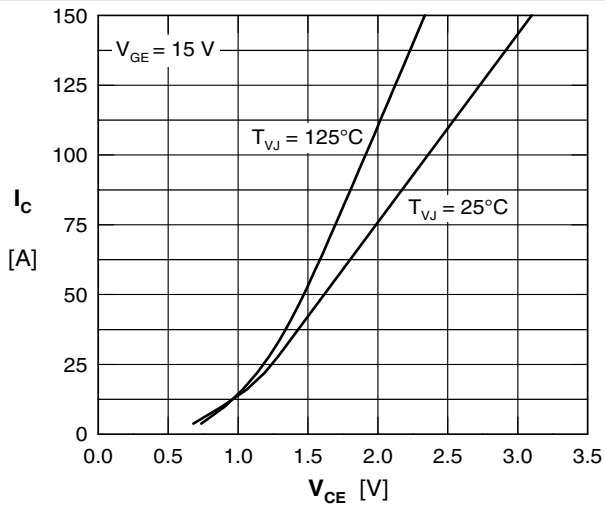


Fig. 1 Typ. output characteristic

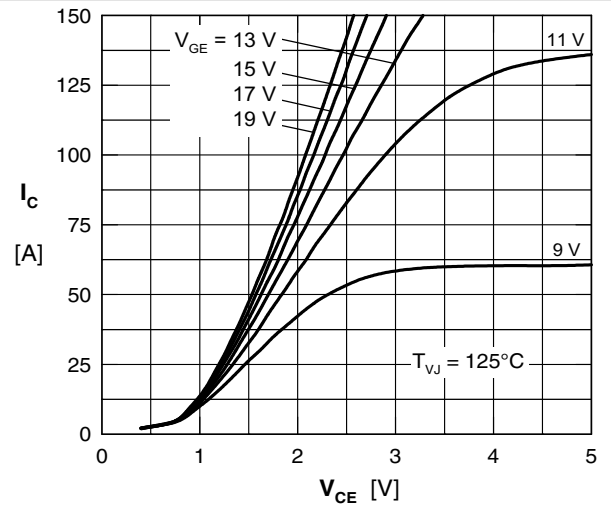


Fig. 2 Typ. output characteristic

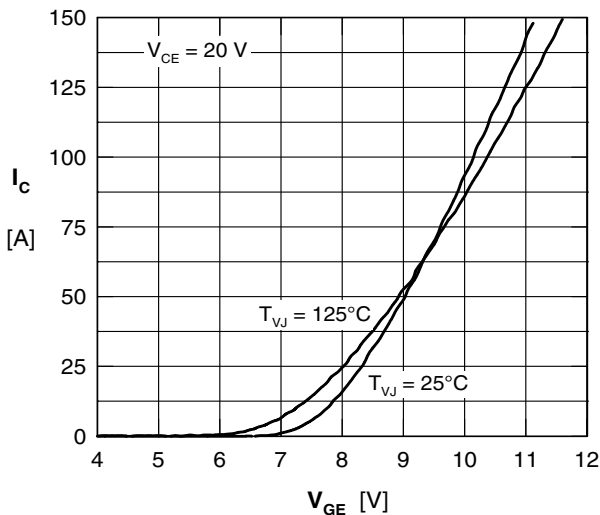


Fig. 3 Typ. transfer characteristic

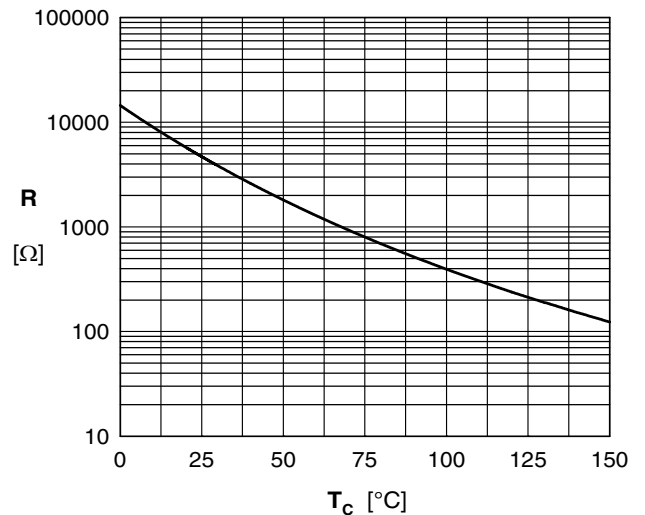


Fig. 4 Typ. NTC resistance versus temperature

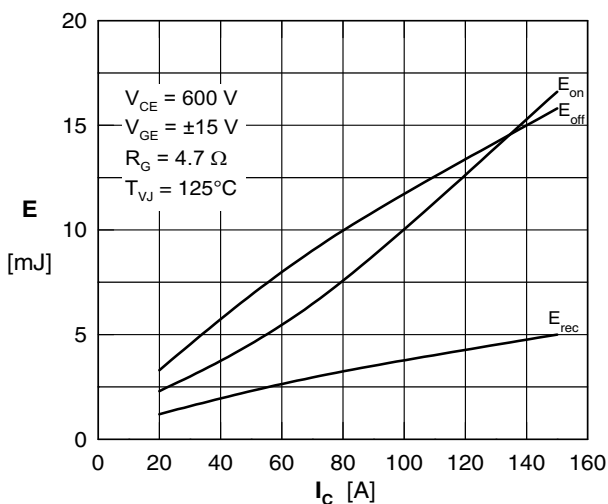


Fig. 5 Typ. switching losses versus collector current impedance

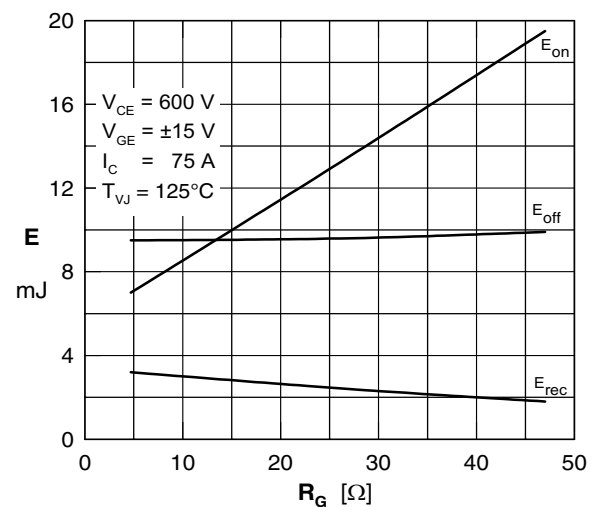


Fig. 6 Typ. switching losses vs. gate resistance

Inverter D1 - D6

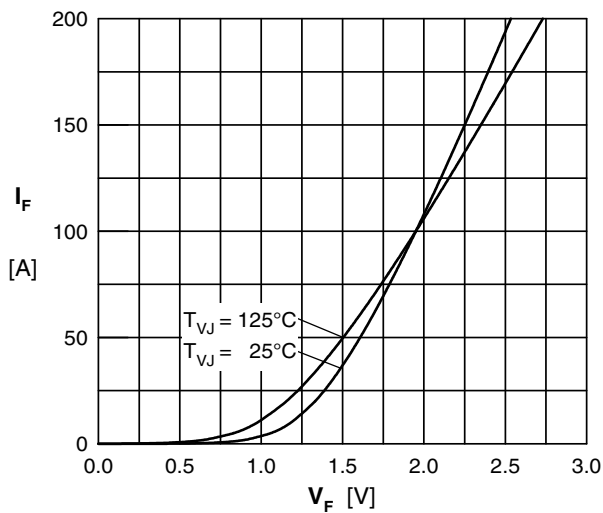


Fig. 7 Typ. Forward current versus V_F

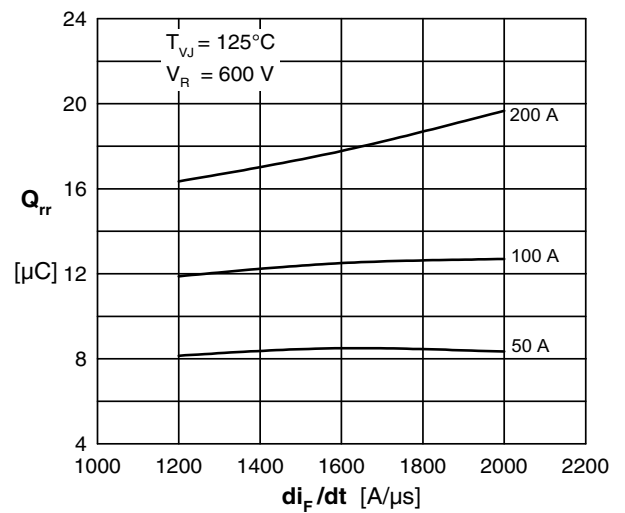


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

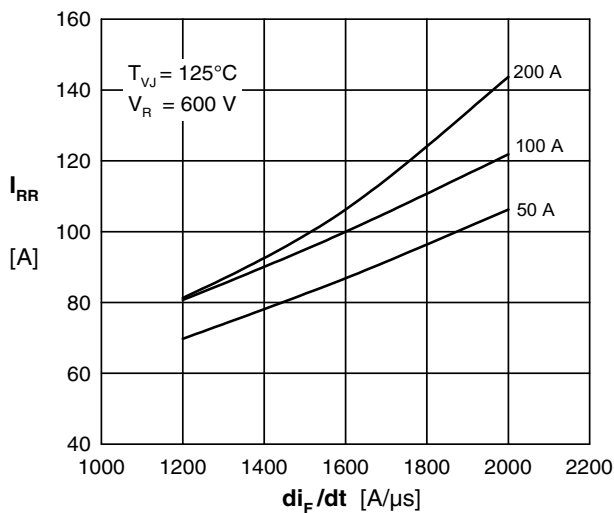


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

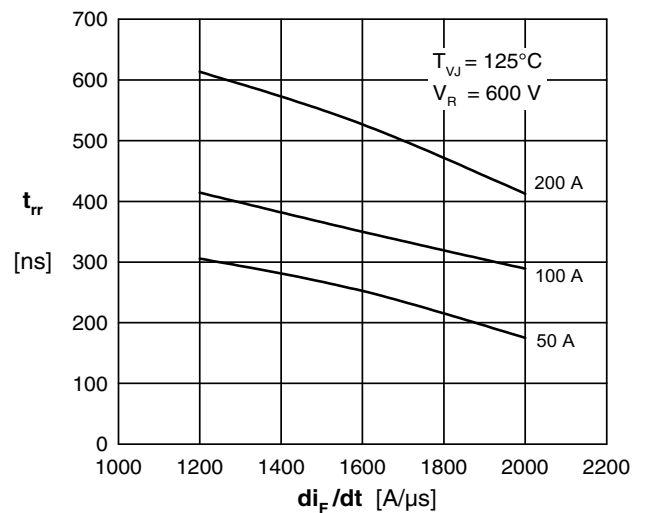


Fig. 10 Typ. recovery time t_{rr} versus di/dt

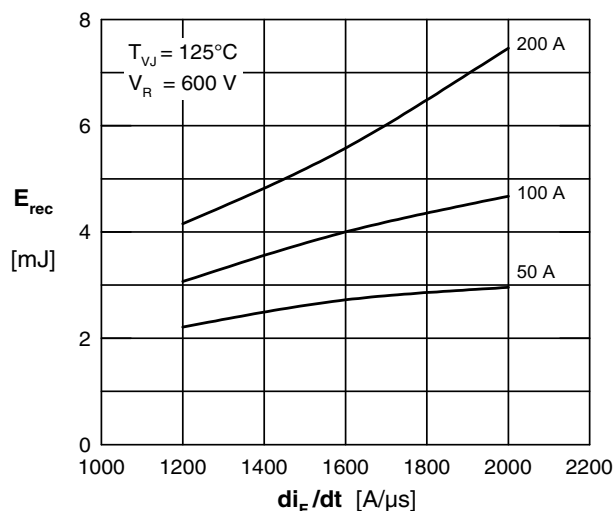


Fig. 11 Typ. recovery energy E_{rec} versus di/dt

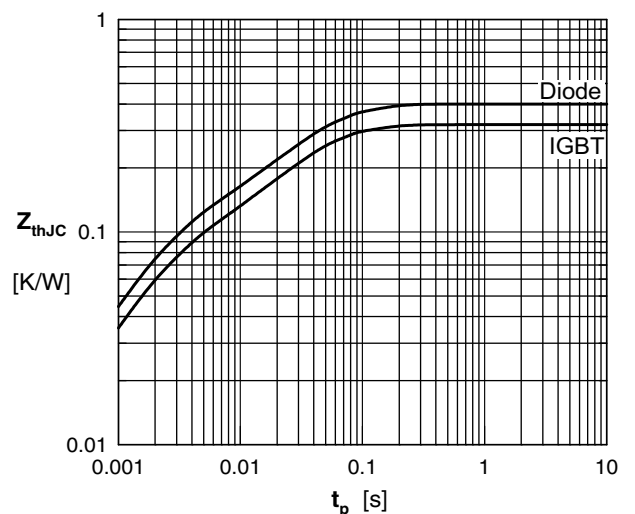


Fig. 12 Typ. transient thermal impedance